1 Megabit

 $(128K \times 8)$

Erasable

CMOS

EPROM

UV

Low Voltage

Features

- Wide Power Supply Range, 3.0 VDC to 5.5 VDC
- Compatible with JEDEC Standard AT27C010
- Low Power 3-Volt CMOS Operation 100 uA max. Standby 26 mW max. Active at 1 MHz for Vcc = 3.3 VDC 138 mW max. Active at 5 MHz for Vcc = 5.5 VDC
- Read Access Time 250 ns
- Wide Selection of JEDEC Standard Packages including OTP 32-Lead 600-mil Cerdip and OTP Plastic DIP and SOIC 32-Pad LCC, 32-Lead JLCC, OTP PLCC and TSOP
- High Reliability CMOS Technology 2000 V ESD Protection 200 mA Latchup Immunity
- Rapid Programming 100 µs/byte (typical)
- **Two-line Control**
- **CMOS and TTL Compatible Inputs and Outputs**
- Integrated Product Identification Code
- Commercial and Industrial Temperature Ranges

Description

The AT27LV010 chip is a low power, low voltage 1,048,576 bit Ultraviolet Erasable and Electrically Programmable Read Only Memory (EPROM) organized as 128K x 8 bits. It requires only one supply in the range of 3.0 to 5.5 VDC in normal read mode operation, making it ideal for battery powered systems.

With a typical power draw of only 18mW at 1 MHz and Vcc at 3.3 VDC, the AT27LV010 will draw less than one-fifth the power of a standard 5-volt EPROM. Standby mode supply current is typically less than 10 µA.

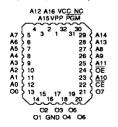
Pin Configurations

Pin Name	Function
A0-A16	Addresses
00-07	Outputs
CE	Chip Enable
ŌĒ	Output Enable
PGM	Program Strobe
NC	No Connect

	$\overline{}$		1
VPP C	1 ~	32	PGM NC
A16 C	1 2 3 4 5 6 7 8 9	32 31	PGM NC
A15 C A12 C A7 C A6 C A5 C A4 C A2 C A1 C A0 C	3	30	Þ NC
A12 E	4	29	D A14
A7 E	5	28	A14 A13 A8 A9 A11 OE A10 CE O7
A6 E	6	27	P A8
A5 C	7	26	ÞΑ9
A4 [8	25	P A11
A3 [9	24	Þ Œ
A2 [10	23	P A10
A1 C	11	22	D CE
AO C	12	21	P 07
O0 E	13	20	D O6
O1 E	14	19	₽ 05
A16 C A16 C A12 C A7 C A6 C A5 C A2 C A1 C A0 C O1 C O2 C GND C	11 12 13 14 15	30 29 28 27 26 25 24 23 22 21 20 19 18	06 05 004 003
GND C	16	17	Po₃
			,

CDIP, PDIP, SOIC Top View

LCC, JLCC, PLCC Top View



TSOP Top View

		iype i			
A11 A9 A00 A13 A14 A13 A14 A15 A15 A12 A15 A14 A15 A14 A15 A14 A15 A15 A14 A15 A15 A14 A15	0 1 2 3 6 5 6 7 8 9 10 11 12 13 16 15		32 30 29 28 27 26 25 24 23 22 21 20 19 18 17	A1 07 05 05 05 05 05 05 05 05 05 05 05 05 05	O6 O4 GND O1 A0



4-55

1074177 0005296 695 **I**



Description (Continued)

The AT27LV010 comes in a choice of industry standard JEDEC-approved through hole and surface mount packages including windowed and one time programmable (OTP) packages, such as the OTP thin small outline package (TSOP). All devices feature two line control ($\overline{\text{CE}}$, $\overline{\text{OE}}$) to give designers the flexibility to prevent bus contention.

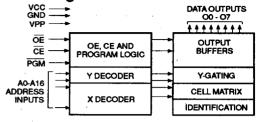
The AT27LV010 operating with V_{CC} at 3.0 VDC produces TTL level outputs that are compatible with standard TTL logic devices operating at V_{CC} = 5.0 VDC.

Atmel's 27LV010 has additional features to ensure high quality and efficient production use. The Rapid Programming Algorithm reduces the time required to program the part and guarantees reliable programming. Programming time is typically only 100 μs /byte. The Integrated Product Identification Code electronically identifies the device and manufacturer. This feature is used by industry standard programming equipment to select the proper programming algorithms and voltages. The AT27LV010 programs identically as an AT27C010.

Erasure Characteristics

The entire memory array of the AT27LV010 is erased (all outputs read as VoH) after exposure to ultraviolet light at a wavelength of 2537 Å. Complete erasure is assured after a minimum of 20 minutes exposure using 12,000 $\mu\text{W/cm}^2$ intensity lamps spaced one inch away from the chip. Minimum erase time for lamps at other intensity ratings can be calculated from the minimum integrated erasure dose of 15 W-sec/cm 2 . To prevent unintentional erasure, an opaque label is recommended to cover the clear window on any UV erasable EPROM which will be subjected to continuous fluorescent indoor lighting or sunlight.

Block Diagram



Absolute Maximum Ratings*

Temperature Under Bias40°C to +85°C	
Storage Temperature65°C to +125°C	
Voltage on Any Pin with Respect to Ground2.0 V to +7.0 V ⁽¹⁾	
Voltage on A9 with Respect to Ground2.0 V to +14.0 V ⁽¹⁾	
Vpp Supply Voltage with Respect to Ground2.0 V to +14.0 V ⁽¹⁾	
Integrated UV Erase Dose7258 W-sec/cm ²	

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.

This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Notes:

Minimum voltage is -0.6 V dc which may undershoot to -2.0 V for pulses of less than 20 ns. Maximum output pin voltage is V_{CC} + 0.75 V dc which may be exceeded if certain precautions are observed (consult application notes) and which may overshoot to +7.0 V for pulses of less than 20 ns.

Operating Modes

Mode \ Pin	CE	ŌĒ	PGM	Ai	Vpp	Vcc	Outputs
Read	VįL	VIL	X ⁽¹⁾	Ai	X	Vcc	Dout
Output Disable	X	ViH	Х	X	Х	Vcc	High Z
Standby	VIH	Х	Х	X	х	Vcc	High Z
Fast Program ⁽²⁾	VIL	VIH	VIL	Ai	Vpp	Vcc (2)	Din
PGM Verify ⁽²⁾	VIL	VIL	ViH	Ai	Vpp	Vcc (2)	Dout
PGM Inhibit ⁽²⁾	ViH	X	Х	X	V _{PP}	Vcc (2)	High Z
Product Identification ^{(2),(4)}	VIL	VIL	х	A9=V _H ⁽³⁾ A0=VIH or VIL A1-A16=VII	х	Vcc ⁽²⁾	Identification Code

Notes: 1. X can be VIL, or VIH.

- Refer to Programming characteristics. Programming modes require V_{CC} > 4.5 V.
- 3. $V_H = 12.0 \pm 0.5 \text{ V}.$

4. Two identifier bytes may be selected. All Ai inputs are held low (V_{IL}), except A9 which is set to V_H and A0 which is toggled low (V_{IL}) to select the Manufacturer's Identification byte and high (V_{IH}) to select the Device Code byte.

4-56

AT27LV010

1074177 0005297 521 🖿

D.C. and A.C. Operating Conditions for Read Operation

		AT27LV010		
		-25	-30	
Operating Temperature	Com.	0°C - 70°C	0°C - 70°C	
(Case)	Ind.	-40°C - 85°C	-40°C - 85°C	
Vcc Power Supply		3.0 V to 5.5 V	3.0 V to 5.5 V	

D.C. and Operating Characteristics for Read Operation

(VCC = 3.0 V to 5.5 V unless otherwise specified)

Symbol	Parameter	Condi	tion		Min	Max	Units
Ē	Input Load Current	VIN = -	0.1 V to Vcc+1 V			5	μА
llo	Output Leakage Current	Vout =	= -0.1 V to Vcc+0.1 V			10	μА
lpp1 ⁽²⁾	V _{PP} ⁽¹⁾ Read/Standby Current	V _{PP} =	Vcc-0.7 V to Vcc+0.3 V			10	μA
IsB	V _{CC} ⁽¹⁾ Standby Current	ISB1 (CMOS), CE = Vcc-0.3 to Vcc+1.0 V		•		100	μА
		Isaz (T	IsB2 (TTL), CE=2.0 to Vcc+1.0 V			1	mA
	C Vcc Active Current	, f = 5 MHz, lou	f = 5 MHz, lout = 0 mA,	Com.		25	mA
lcc		Icc1	CE = VIL, VCC = 5.5 V	Ind.		30	mA
100		ICC2 $\frac{f = 1 \text{ MHz, lout} = 0 \text{ mA}}{CE} = V_{IL}, V_{CC} = 3.3 \text{ V}$	f = 1 MHz, lour = 0 mA	Com.		8	mA
			Ind.		10	mA	
ViL	Input Low Voltage				-0.6	0.8	٧
ViH	Input High Voltage				2.0	Vcc+0.75	V
Vol	Output Low Voltage	lot = 2	2.1 mA			.45	٧
	Output High Vallage	1он = -	-100 μA		Vcc-0.0	3	٧
Vон	Output High Voltage	IOH = -400 μA			2.4		V

Notes: 1. V_{CC} must be applied simultaneously or before V_{PP} , and removed simultaneously or after V_{PP} .

A.C. Characteristics for Read Operation (VCC = 3.0V to 5.5V)

				AT27LV010)		
				-2	25	-3	30	
Symbol	Parameter	Condition		Min	Max	Min	Max	Units
tacc (3)	Address to Output Delay	CE = OE = VII	Com.		250		270	ns
Address to Outpu	Address to Output Delay	OE = OE = VIL	Ind.		250		270	ns
tce (2)	CE to Output Delay	OE = VIL			250		300	ns
toE (2,3)	OE to Output Delay	CE = VIL	·		100		150	ns
toF (4,5)	OE High to Output Float	CE = ViL			50		50	ns
tон	Output Hold from Address, CE or OE, whichever occurred first	CE = OE = VIL		0		0		ns

Notes: 2, 3, 4, 5. - see AC Waveforms for Read Operation.



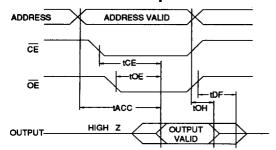
4-57

■ 1074177 0005298 468 ■

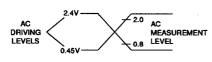
^{2.} V_{PP} may be connected directly to V_{CC} , except during programming. The supply current would then be the sum of I_{CC} and I_{PP} .



A.C. Waveforms for Read Operation (1)



Input Test Waveform and Measurement Level



t_R, t_F < 20 ns (10% to 90%)

Notes:

- Timing measurement references are 0.8 V and 2.0 V. Input AC driving levels are 0.45 V and 2.4 V. See Input Test Waveforms and Measurement Levels.
- OE may be delayed up to t_{CE}-t_{OE} after the falling edge of CE without impact on t_{CE}.
- OE may be delayed up to tACC-toE after the address is valid without impact on tACC.
- 4. This parameter is only sampled and is not 100% tested
- Output float is defined as the point when data is no longer driven.

Output Test Load



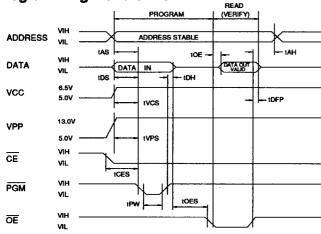
Note: $C_L = 100 \text{ pF}$ including jig capacitance.

Pin Capacitance $(f = 1 \text{ MHz}, T = 25^{\circ}\text{C})^{(1)}$

	Тур	Max	Units	Conditions	
Cin	4	8	pF	VIN = 0 V	
Соит	8	12	pF	Vout = 0 V	

Notes: 1. Typical values for 5-V supply voltage. This parameter is only sampled and is not 100% tested,

Programming Waveforms (1)



Notes:

- 1. The Input Timing Reference is 0.8 V for V_{IL} and 2.0 V for V_{IH} .
- toe and topp are characteristics of the device but must be accommodated by the programmer.
- When programming the AT27LV010 a 0.1-μF capacitor is required across Vpp and ground to suppress spurious voltage transients.

4-58

AT27LV010

■ 1074177 0005299 3T4 ■

D.C. Programming Characteristics

 $T_A = 25 \pm 5^{\circ}C$, $V_{CC} = 6.5 \pm 0.25 \text{ V}$, $V_{PP} = 13.0 \pm 0.25 \text{ V}$

Sym-		Test	Lir	nits	
bol	Parameter	Conditions	Min	Max	Units
ILI	Input Load Current	VIN=VIL,VIH		10	μΑ
VIL	Input Low Level	(All Inputs)	-0.6	0.8	٧
ViH	Input High Level		2.0	Vcc+1	٧
Vol	Output Low Volt.	lot=2.1 mA		.45	٧
Vон	Output High Volt.	Юн=-400 μА	2.4		٧
lcc2	Vcc Supply Curren (Program and Ver			40	mA
IPP2	V _{PP} Supply Current	CE=PGM=VIL		20	mA
VID	A9 Product Identification Voltage		11.5	12.5	٧

A.C. Programming Characteristics

 $T_A = 25 \pm 5^{\circ}C$, $V_{CC} = 6.5 \pm 0.25 \text{ V}$, $V_{PP} = 13.0 \pm 0.25 \text{ V}$

Sym-		Test Conditions*	Lir	nits	
bol	Parameter	(see Note 1)	Min	Max (Jnits
tas	Address Setup Tin	ne	2		μS
tces	CE Setup Time		2		μS
toes	OE Setup Time		2		μs
tos	Data Setup Time		2		μs
tan	Address Hold Time	8	0		μS
tDH	Data Hold Time		2		μS
tDFP	OE High to Out- put Float Delay	(Note 2)	0	130	ns
tvps	V _{PP} Setup Time		2		μS
tvcs	V _{CC} Setup Time		2		μ\$
tpw	PGM Program Pulse Width	(Note 3)	95	105	μS
toe	Data Valid from O	Ē		150	ns

*A.C. Conditions of Test:

Input Rise and Fall Times (10% to 90%)	20 ns
Input Pulse Levels	0.45 V to 2.4 V
Input Timing Reference Level	0.8 V to 2.0 V
Output Timing Reference Level	08 V to 20 V

Notes:

- V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.
- This parameter is only sampled and is not 100% tested.
 Output Float is defined as the point where data is no longer driven see timing diagram.
- 3. Program Pulse width tolerance is $100 \, \mu sec \pm 5\%$.

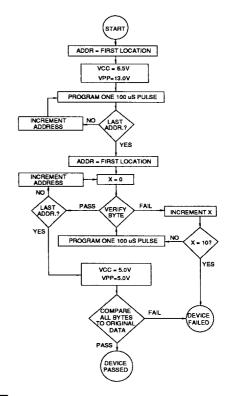
Atmel's 27LV010 Integrated Product Identification Code (1)

		Pins H					Hex			
Codes	AO	07	O 6	O 5	04	ОЗ	02	01	00	Data
Manufacturer	0	0	0	0	1	1	1	1	0	1E
Device Type	1	0	0	0	0	0	1	0	1	O5

Note: 1. The AT27LV010 has the same Product Identification Code as the AT27C010/L. Both are programming compatible.

Rapid Programming Algorithm

A 100 μs \overline{PGM} pulse width is used to program. The address is set to the first location. V_{CC} is raised to 6.5 V and Vpp is raised to 13.0 V. Each address is first programmed with one 100 μs \overline{PGM} pulse without verification. Then a verification/ reprogramming loop is executed for each address. In the event a byte fails to pass verification, up to 10 successive 100 μs pulses are applied with a verification after each pulse. If the byte fails to verify after 10 pulses have been applied, the part is considered failed. After the byte verifies properly, the next address is selected until all have been checked. Vpp is then lowered to 5.0 V and Vcc to 5.0 V. All bytes are read again and compared with the original data to determine if the device passes or fails.





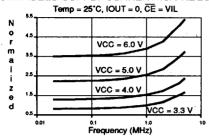
4-59

1074177 0005300 946

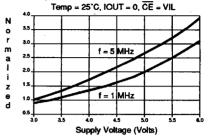


LV EPROM Product Characteristics

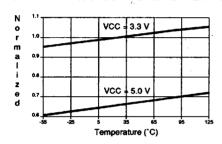
NORMALIZED SUPPLY CURRENT vs. FREQUENCY



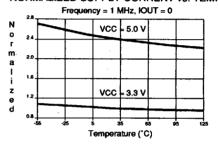
NORMALIZED SUPPLY CURRENT vs. VOLTAGE



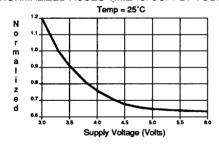
NORMALIZED ACCESS TIME vs. TEMPERATURE



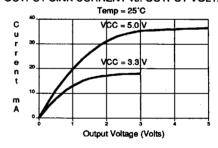
NORMALIZED SUPPLY CURRENT vs. TEMP.



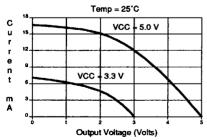
NORMALIZED ACCES TIME vs. SUPPLY VOLTAGE



OUTPUT SINK CURRENT vs. OUTPUT VOLTAGE



OUTPUT SOURCE CURRENT vs. OUTPUT VOLTAGE



AT27LV010

1074177 0005301 882 **1**

4-60

Ordering Information

tacc (ns)	Icc (mA) Vcc = 3.3 V Active Standby		Ordering Code	Package	Operation Range		
250	8	0.1	AT27LV010-25DC AT27LV010-25KC AT27LV010-25LC	32DW6 32KW 32LW	Commercial (0°C to 70°C)		
250	10	0.1	AT27LV010-25DI AT27LV010-25LI	32DW6 32LW	Industrial (-40°C to 85°C)		
300	8	0.1	AT27LV010-30DC AT27LV010-30JC AT27LV010-30KC AT27LV010-30LC AT27LV010-30PC AT27LV010-30RC	32DW6 32J 32KW 32LW 32P6 32R	Commercial (0°C to 70°C)		
300	10	0.1	AT27LV010-30DI AT27LV010-30LI	32DW6 32LW	Industrial (-40°C to 85°C)		

tacc	Icc (mA) Vcc = 3.3 V		Ordering Code Package		Operation Range	
(ns)	Active	Standby				
250	8	0.1	AT27LV010-25TC	32T	Commercial (0°C to 70°C)	
300	8	0.1	AT27LV010-30TC	32T	Commercial (0°C to 70°C)	

	Package Type
32DW6	32 Lead, 0.600" Wide, Windowed, Ceramic Dual Inline Package (Cerdip)
32J	32 Lead, Plastic J-Leaded Chip Carrier OTP (PLCC)
32KW	32 Lead, Windowed, Ceramic J-Leaded Chip Carrier (JLCC)
32LW	32 Pad, Windowed, Ceramic Leadless Chip Carrier (LCC)
32P6	32 Lead, 0.600" Wide, Plastic Dual Inline Package OTP (PDIP)
32R	32 Lead, 0.450" Wide, Plastic Gull Wing Small Outline OTP (SOIC)
32T	32 Lead, Plastic Thin Small Outline Package OTP (TSOP)



4-61

1074177 0005302 719 🖿